

CS/B.Tech/IT/Odd/Sem-7th/IT-705D/2014-15

IT-705D

MICROELECTRONICS AND VLSI DESIGN

Time Allotted: 3 Hours

Full Marks: 70

The questions are of equal value.

The figures in the margin indicate full marks

Candidates are required to give their answers in their own words as far as practicable.

GROUP A
(Multiple Choice Type Questions)

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- (v) Latch up is defined as the.

 - (A) low impedance
 - (B) high impedance
 - (C) medium impedance
 - (D) none

(vi) Designable parameters are.

 - (A) commonly grouped
 - (B) loosely coupled
 - (C) tightly coupled
 - (D) none

(vii) Noise parameters are treated as.

 - (A) static variables
 - (B) random variables
 - (C) constants
 - (D) none

(viii) A circuit performance major is used to monitor

 - (A) functionality of circuit
 - (B) durability of circuit
 - (C) accountability of circuit
 - (D) none

(ix) Designable parameters are

 - (A) deterministic
 - (B) probabilistic
 - (C) indeterministic
 - (D) none

(x) Which among the following requires lowest design cycle time?

 - (A) semi-custom ASIC
 - (B) full-custom ASIC
 - (C) standard cell-based design
 - (D) FPGA

(xi) Different FPGA programming technologies are based on

 - (A) SRAM
 - (B) EPROM
 - (C) Anti-fuse
 - (D) all of these

(xii) The model parameter LAMDA (λ) in a MOS structure stands for

 - (A) flicker noise coefficient
 - (B) transit time
 - (C) channel length modulation
 - (D) transconductance

GROUP B
(Short Answer Type Questions)

Answer any <i>three</i> questions.	$3 \times 5 = 15$
2. (a) What is Layout?	1
(b) Draw the Circuit diagram and Layout of CMOS inverter and explain.	2+2
3. (a) What is Stick Diagram?	1
(b) Draw the Stick diagram of $F = (A + B + C) \cdot D$ and calculate the area using the λ -rule.	4
4. Explain the Y-chart of VLSI design flow.	5
5. What is an FPGA? How is it different from CPLD? What are its advantages?	2+2+1
6. (a) What is ASIC? Give its classification.	2
(b) Why VLSI design flow is often called as cycle? Explain.	3
7. Write VHDL code in behavioral mode for a full Adder.	5

GROUP C
(Long Answer Type Questions)

Answer any <i>three</i> questions.	$3 \times 15 = 45$
8. (a) Explain the <i>n</i> -well CMOS fabrication process with necessary diagram.	10
(b) Draw the CMOS NAND gate and CMOS NOR gate using Layout technique.	5
9. (a) Explain with example and proper block diagram the Standard Cell based design.	8
(b) Explain the Moore's Law for both processor and Memory design.	3
(c) Explain λ -rule.	4

10.(a) Draw the CMOS full Adder circuit. Hence draw the corresponding mask layout diagram.	3+3
(b) Explain the static and dynamic power losses in VLSI design.	4
(c) Why pull up networks are made of <i>p</i> -MOS transistor and Pull down networks are made of <i>n</i> -MOS transistor.	2
11.(a) Draw the circuit diagram of CMOS inverter and calculate the followings (Symbols are of usual meaning)	3+3+3
(i) V_{IL}	1
(ii) V_{IH}	1
(iii) V_{OL}	1
(b) Explain the voltage transfer characteristic VTC of the Inverter.	4
(c) What is uncertain or transition region of the VTC curve, explain.	2
12.(a) Draw the circuit diagram of CMOS NOR based SR Latch and NAND based SR latch.	2.5+2.5
(b) Draw the circuit diagram of CMOS master slave JK flip flop and explain its timing diagram.	4+3
(c) Draw the circuit diagram of CMOS clocked D-flip flop	3
13. Write short notes on any <i>three</i> of the following:	3×5

- (a) Dynamic logic
- (b) Photo-lithography
- (c) Ion-implantation
- (d) PLA
- (e) Latch up problem in CMOS